



STW220NF75

N-CHANNEL 75V - 0.004 Ω - 120A TO-247 STripFET™ II POWER MOSFET

TYPE	V _{DSS}	R _{DS(on)}	I _D
STW220NF75	75V	<0.0044Ω	120A(**)

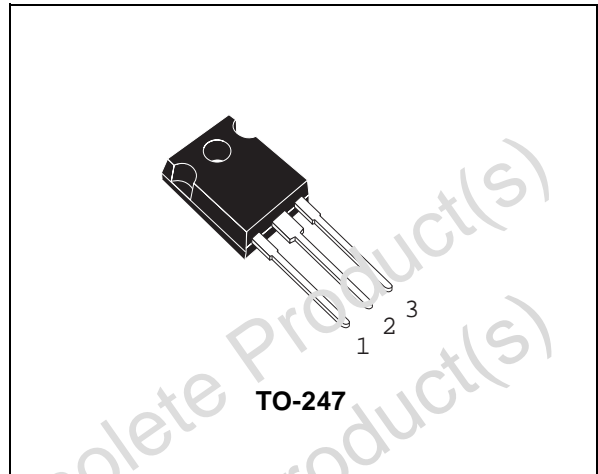
- TYPICAL R_{DS(on)} = 0.004Ω
- STANDARD THRESHOLD DRIVE
- 100% AVALANCHE TESTED

DESCRIPTION

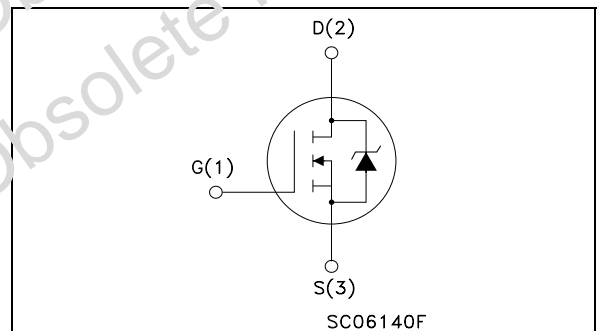
This Power MOSFET is the latest development of STMicroelectronics unique "Single Feature Size™" strip-based process. The resulting transistor shows extremely high packing density for low on-resistance, rugged avalanche characteristics and less critical alignment steps therefore a remarkable manufacturing reproducibility.

APPLICATIONS

- HIGH CURRENT, HIGH SWITCHING SPEED
- AUTOMOTIVE 42V BATTERY SYSTEM
- OR-ING FUNCTION



INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DS}	Drain-source Voltage (V _{GS} = 0)	75	V
V _{DGF}	Drain-gate Voltage (R _{GS} = 20 kΩ)	75	V
V _{GS}	Gate- source Voltage	± 20	V
I _{D(*)}	Drain Current (continuous) at T _C = 25°C	120	A
I _{D(**)}	Drain Current (continuous) at T _C = 100°C	120	A
I _{DM(*)}	Drain Current (pulsed)	480	A
P _{tot}	Total Dissipation at T _C = 25°C	500	W
	Derating Factor	3.33	W/°C
dv/dt (1)	Peak Diode Recovery voltage slope	10	V/ns
E _{AS(2)}	Single Pulse Avalanche Energy	2500	mJ
T _{stg}	Storage Temperature	-55 to 175	°C
T _j	Operating Junction Temperature		

•) Pulse width limited by safe operating area.
(**) Current Limited by Package

(1) I_{SD} ≤ 120A, di/dt ≤ 100A/μs, V_{DD} ≤ V_{(BR)DSS}, T_j ≤ T_{JMAX}
(2) Starting T_j = 25 °C, I_D = 60 A, V_{DD} = 30V

STW220NF75**THERMAL DATA**

Rthj-case	Thermal Resistance Junction-case	Max	0.30	°C/W
Rthj-amb	Thermal Resistance Junction-ambient	Max	50	°C/W
T _j	Maximum Lead Temperature For Soldering Purpose (1.6 mm from case, for 10 sec)	Typ	300	°C

ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{(BR)DSS}	Drain-source Breakdown Voltage	I _D = 250 μA, V _{GS} = 0	75			V
I _{DSS}	Zero Gate Voltage Drain Current (V _{GS} = 0)	V _{DS} = Max Rating V _{DS} = Max Rating T _C = 125°C			1 10	μA μA
I _{GSS}	Gate-body Leakage Current (V _{DS} = 0)	V _{GS} = ± 20V			±100	nA

ON (1)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} I _D = 250 μA	2		4	V
R _{DS(on)}	Static Drain-source On Resistance	V _{GS} = 10 V I _D = 60 A		0.004	0.0044	Ω

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g _{fs} (*)	Forward Transconductance	V _{DS} = 25 V I _D = 60 A		200		S
C _{iss}	Input Capacitance	V _{DS} = 25V, f = 1 MHz, V _{GS} = 0		12500		pF
C _{oss}	Output Capacitance			2150		pF
C _{rss}	Reverse Transfer Capacitance			600		pF

ELECTRICAL CHARACTERISTICS (continued)

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on Delay Time Rise Time	$V_{DD} = 38\text{ V}$ $I_D = 60\text{ A}$ $R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$ (Resistive Load, Figure 3)		50 215		ns ns
Q_g Q_{gs} Q_{gd}	Total Gate Charge Gate-Source Charge Gate-Drain Charge	$V_{DD}=38\text{V}$ $I_D=120\text{A}$ $V_{GS}=10\text{V}$		350 60 135	430	nC nC nC

SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(off)}$ t_f	Turn-off Delay Time Fall Time	$V_{DD} = 38\text{ V}$ $I_D = 60\text{ A}$ $R_G = 4.7\ \Omega$, $V_{GS} = 10\text{ V}$ (Resistive Load, Figure 3)		250 130		ns ns

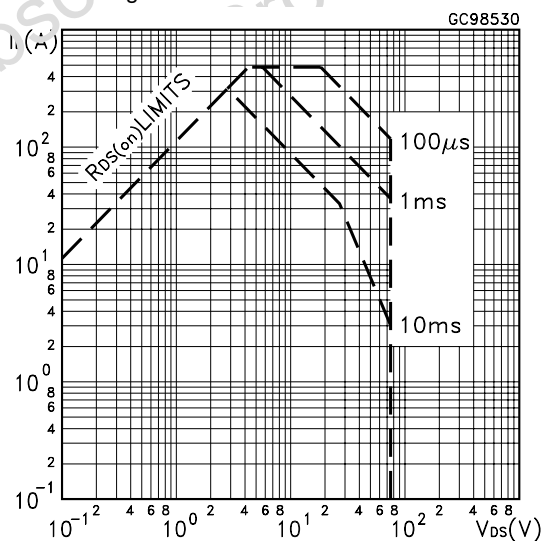
SOURCE DRAIN DIODE

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD} $I_{SDM} (\bullet)$	Source-drain Current Source-drain Current (pulsed)				120 480	A A
$V_{SD} (*)$	Forward On Voltage	$I_{SD} = 120\text{ A}$ $V_{GS} = 0$			1.5	V
t_{rr} Q_{rr} I_{RRM}	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	$I_{SD} = 120\text{ A}$ $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 32\text{ V}$ $T_j = 150^\circ\text{C}$ (see test circuit, Figure 5)		140 770 11		ns nC A

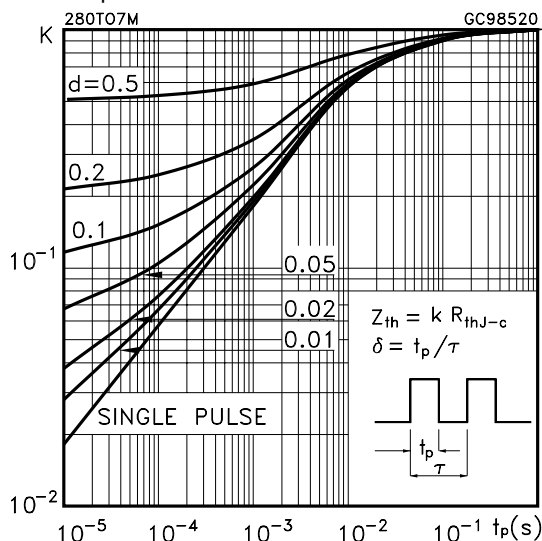
(*) Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %.

(\bullet) Pulse width limited by safe operating area.

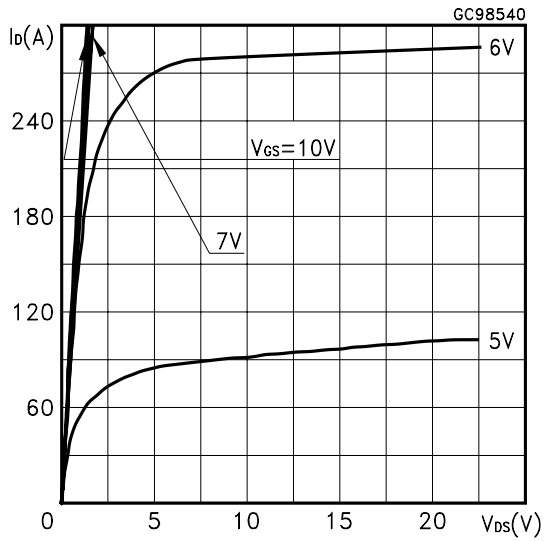
Safe Operating Area



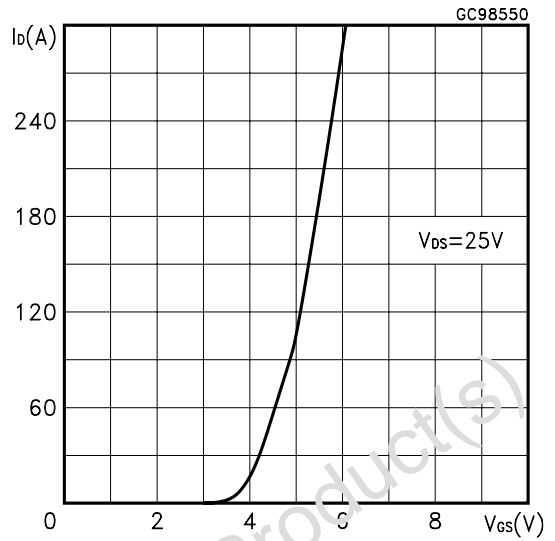
Thermal Impedance



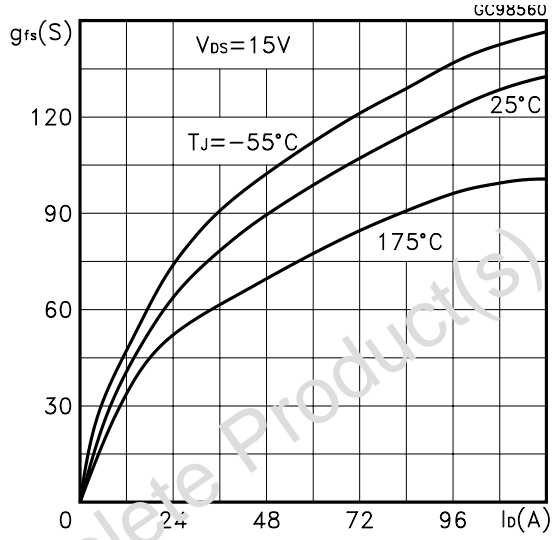
Output Characteristics



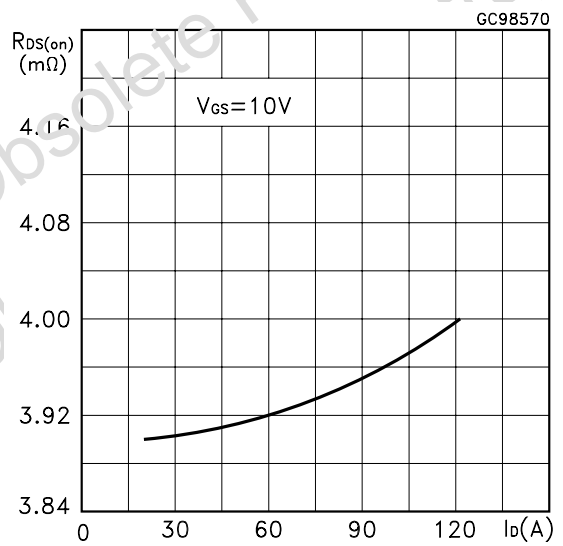
Transfer Characteristics



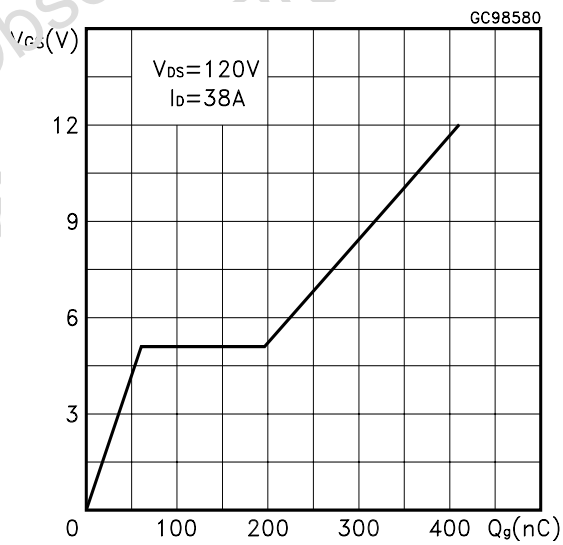
Transconductance



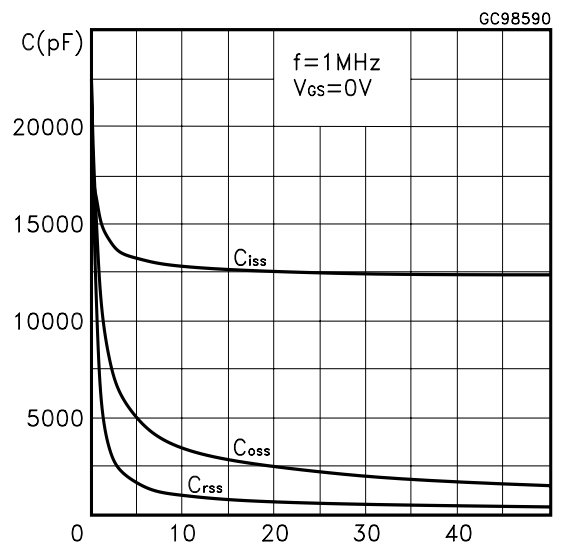
Static Drain-source On Resistance



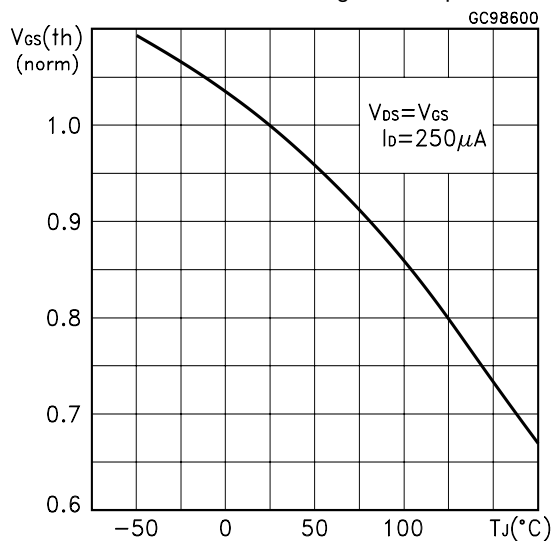
Gate Charge vs Gate-source Voltage



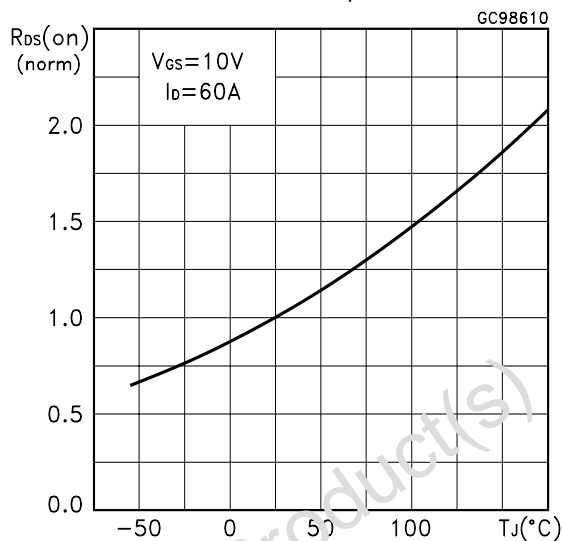
Capacitance Variations



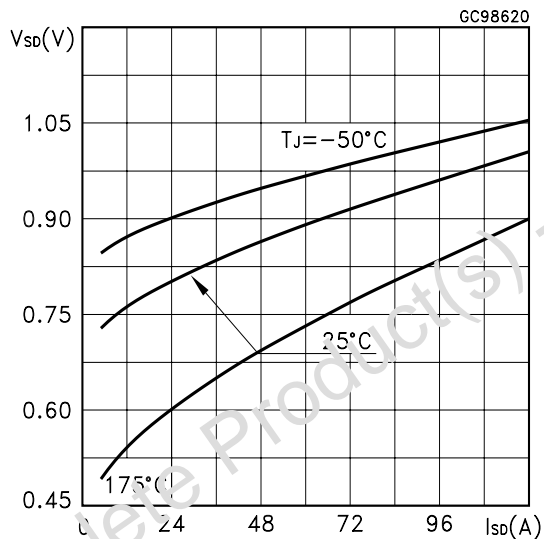
Normalized Gate Threshold Voltage vs Temperature



Normalized on Resistance vs Temperature



Source-drain Diode Forward Characteristics



Normalized Breakdown Voltage vs Temperature

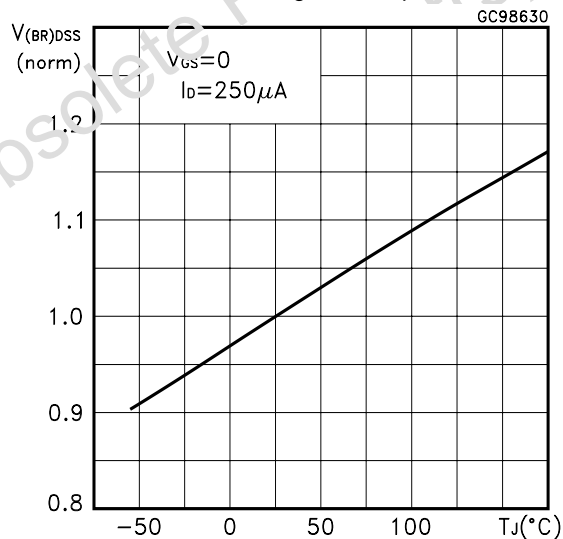


Fig. 1: Unclamped Inductive Load Test Circuit



Fig. 2: Unclamped Inductive Waveform

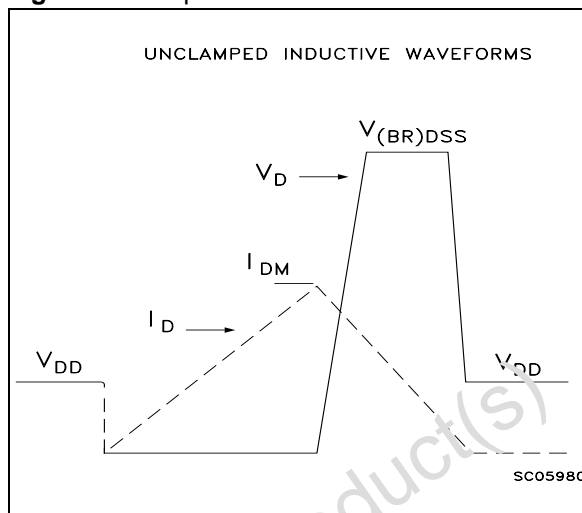


Fig. 3: Switching Times Test Circuits For Resistive Load

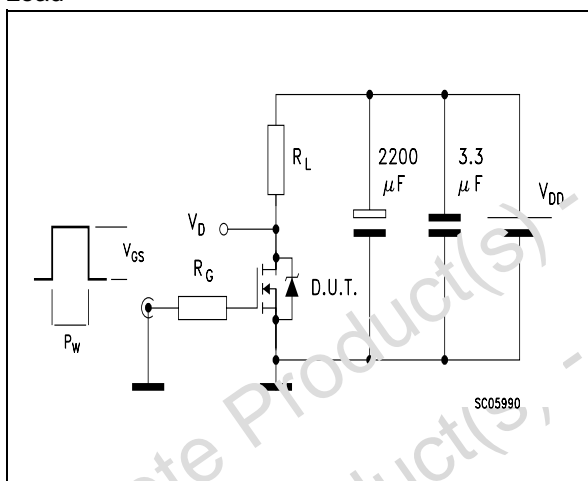


Fig. 4: Gate Charge test Circuit

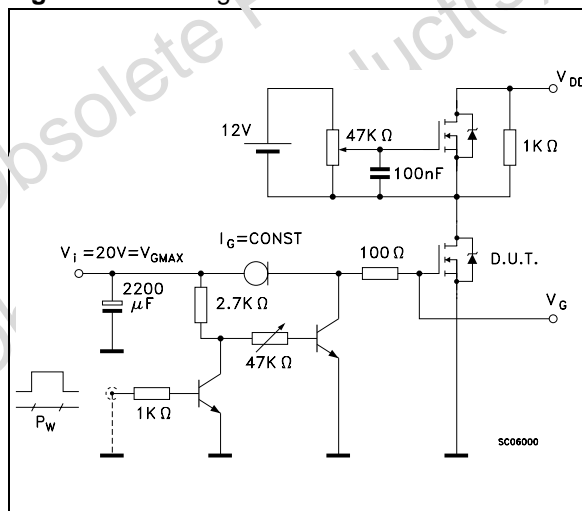
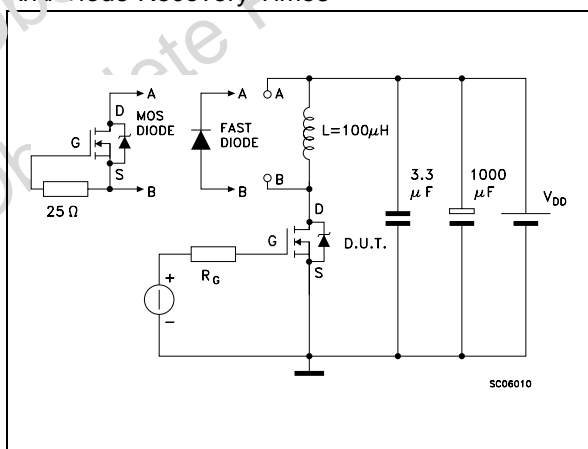
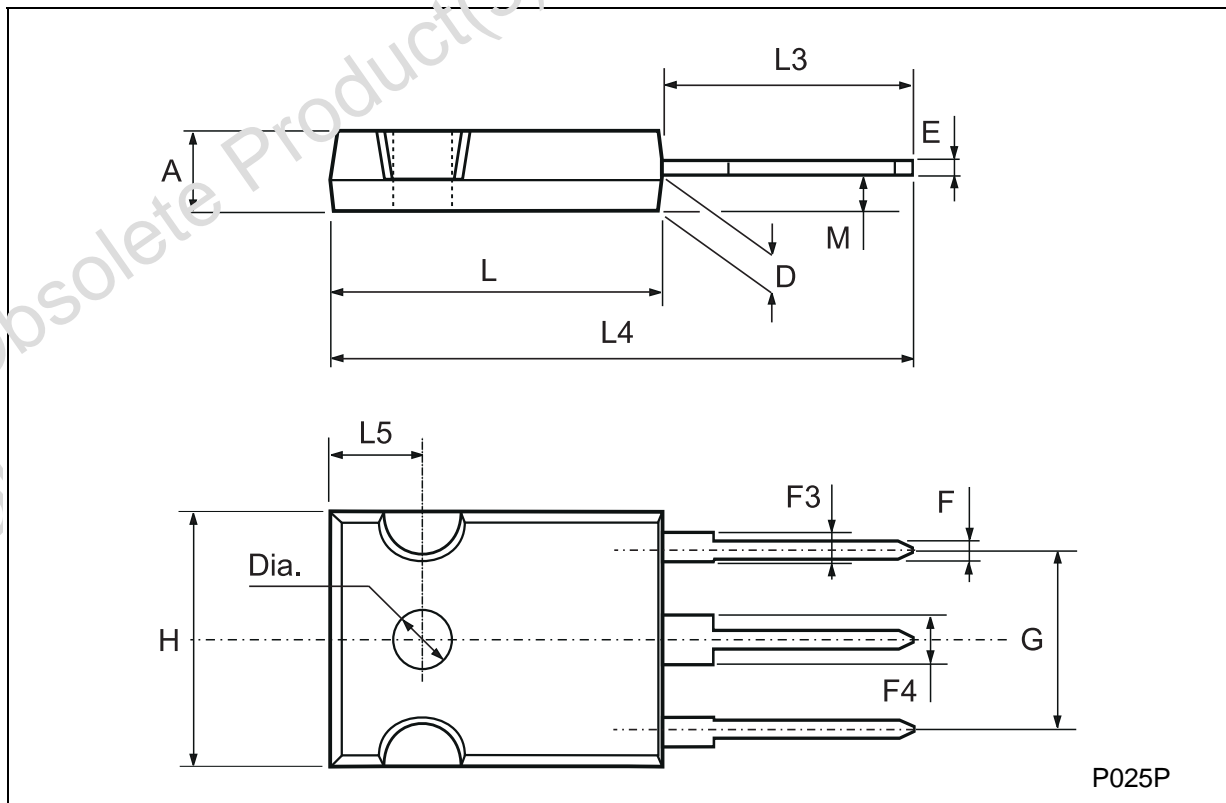


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



TO-247 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.7		5.3	0.185		0.209
D	2.2		2.6	0.087		0.102
E	0.4		0.8	0.016		0.031
F	1		1.4	0.039		0.055
F3	2		2.4	0.079		0.094
F4	3		3.4	0.118		0.134
G		10.9			0.429	
H	15.3		15.9	0.602		0.626
L	19.7		20.3	0.776		0.779
L3	14.2		14.8	0.559		0.582
L4		34.6			1.362	
L5		5.5			0.217	
M	2		3	0.079		0.118



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